



DATA SHEET

M41256xx-10B, -12B, & -15B Dynamic RAM

FEATURES

- 262,144 words \times 1-bit organization
- 100/120/150 ns access time from \overline{RE}
- 50/60/75 ns access time from \overline{CE}
- 385/360/330 mW active power, Page Mode, 413/385/360 mW active power, Nibble Mode, at minimum cycle time
- 25 mW standby power
- Multiplexed address inputs
- $\pm 10\%$ power supply tolerance
- Read-Modify-Write capabilities
- \overline{RE} Only Refresh/Hidden Refresh
- Latched or high impedance output during refresh
- 256 refresh cycles
- Nibble Mode/Page Mode options
- \overline{CE} before \overline{RE} refresh with Nibble Mode Option
- Available in 2 plastic or hermetic ceramic DIP, plastic leaded chip carrier (PLCC), and hermetic ceramic leadless chip carrier (LCC)

DESCRIPTION

The M41256xx-10B, -12B, & -15B integrated circuits are high-speed, low-power 262,144 words by 1-bit dynamic random access memory (DRAM) devices. These devices are available with various mode, speed, and package options.

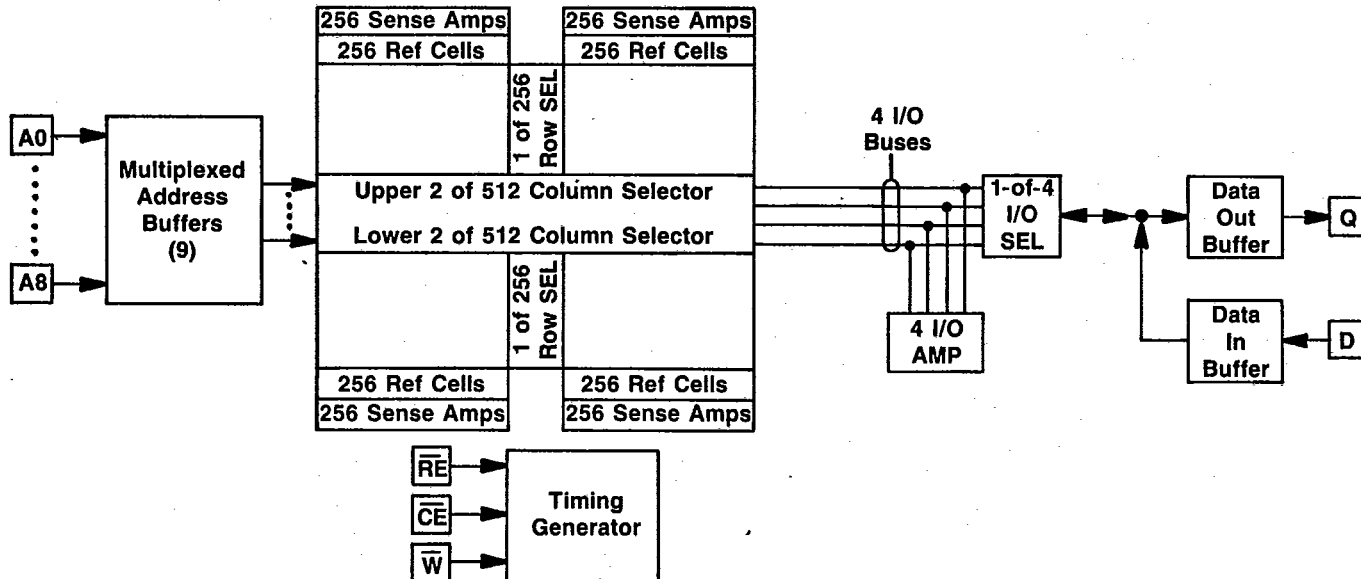


Figure 1. Page Mode Block Diagram

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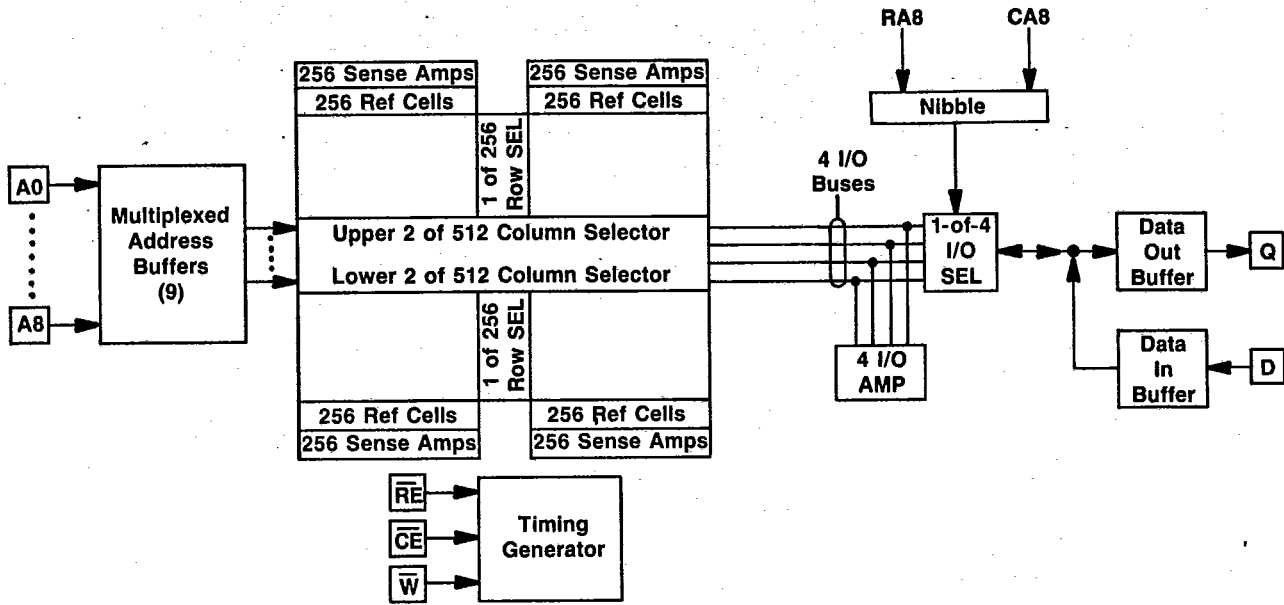
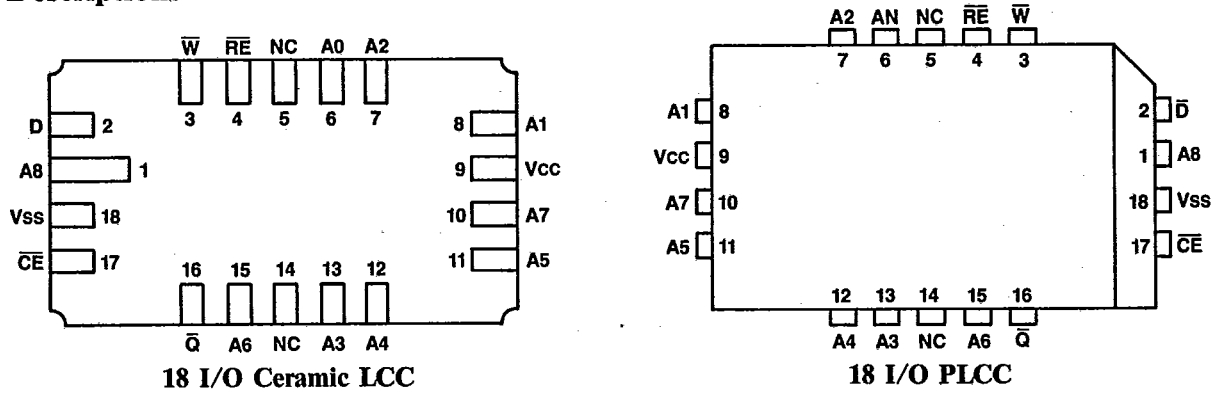


Figure 2. Nibble Mode Block Diagram

USER INFORMATION

Pin Descriptions



Pin Description Key	
Symbol	Name
Vcc	+5 V Supply
D	Data In
Q	Data Out
A(0-8)	Address Input (0-8)
\bar{W}	Write Enable
\bar{RE}	Row Enable
\bar{CE}	Column Enable
Vss	Ground
NC	No Connect

Figure 3. Pin Function Diagram

CHARACTERISTICS

Operating Conditions ($T_A = 0$ to 70°C)

Parameter	Symbol	Min	Nom	Max	Unit
Supply Voltages	VCC	4.5	5.0	5.5	V
	VSS	0	0	0	V
Input Voltages*					
High Level — All Inputs (Logic 1)	V _{IH}	2.4	—	6.5	V
Low Level — All Inputs (Logic 0)	V _{IL}	-1.0	—	0.8	V
Refresh Cycle Time**	t _{REF}	—	—	4.0	ms

* Application of invalid levels may destroy stored information during that cycle as well as the first cycle using valid levels. Data out is indeterminate.

** Addresses A0—A7 are used for refresh. A8 must be a valid one or zero.

Electrical Characteristics

($V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $T_A = 0$ to 70°C)

Parameter	Symbol	M41256xx-10B		M41256xx-12B		M41256xx-15B		Unit
		Min	Max	Min	Max	Min	Max	
Output Voltages								
Low Level ($I_{OL} = 4.2\text{ mA}$)	V _{OL}	—	0.4	—	0.4	—	0.4	V
High Level ($I_{OH} = -5.0\text{ mA}$)	V _{OH}	2.4	—	2.4	—	2.4	—	V
Power Supply Currents								
Operating Current (Average Operating Current \overline{RE} & \overline{CE} Cycling, t _{RELREL} = minimum)								
Page Mode Option	ICC1	—	70†	—	65†	—	60†	mA
Nibble Mode Option	ICC1	—	75†	—	70†	—	65†	mA
Standby Current ($\overline{RE} = V_{IH}$, Q = High Impedance)	ICC2	—	4.5	—	4.5	—	4.5	mA
Refresh Current (Average Operating Current, Refresh Mode Operation) \overline{RE} Cycling, $\overline{CE} = V_{IH}$, t _{RELREL} = min.								
Page Mode Option	ICC3	—	55†	—	50†	—	45†	mA
Nibble Mode Option	ICC3	—	60†	—	55†	—	50†	mA
\overline{CE} before \overline{RE} Nibble Mode Option	ICC3	—	95†	—	90†	—	85†	mA
Page Mode Current (Average Operating Current, Page Mode Operation, $\overline{RE} = V_{IL}$, \overline{CE} Cycling, t _{CELCEL} = minimum)	ICC4	—	50†	—	45†	—	40†	mA
Nibble Mode Current (Average Operating Current, Nibble Mode Operation, $\overline{RE} = V_{IL}$, \overline{CE} Cycling, t _{NCELCEL} = minimum)	ICC5	—	55†	—	50†	—	45†	mA

† Maximum occurs at $T_A = 0^\circ\text{C}$. ICC1, ICC3, ICC4, and ICC5 are specified with output open-circuited.

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Parameter	Symbol	M41256xx-10B		M41256xx-12B		M41256xx-15B		Unit
		Min	Max	Min	Max	Min	Max	
Input Leakage Current (VCC = 5.5 V, VI = 0 to 6.5 V, All other leads at 0 V)	II	-10	10	-10	10	-10	10	μ A
Output Leakage Current (Q = High Impedance, VQ = 0 to VCC)	IO	-10	10	-10	10	-10	10	μ A
Input Capacitance (A0-A8)††	CI1	-	5	-	5	-	5	pF
Input Capacitance (D, \bar{W} Leads)††	CI2	-	5	-	5	-	5	pF
Input Capacitance ($\bar{R}\bar{E}$, $\bar{C}\bar{E}$ Leads)††	CI3	-	10	-	10	-	10	pF
Output Capacitance (Q Lead)††	CO	-	7	-	7	-	7	pF

†† Parameter periodically sampled and not 100% tested.

Maximum Ratings*

Rating	Symbol	Value	Unit
Voltage Range on VCC Relative to VSS	VCC	-1.0 to +7.0	V
Power Dissipation	PD	1.0	W
Case Operating Temperature Range	TC	0 to 85	$^{\circ}$ C
Ambient Operating Temperature Range	TA	0 to 70	$^{\circ}$ C
Ambient Storage Temperature Range**	Tstg		
Ceramic Package		-65 to +160	$^{\circ}$ C
Plastic Package		-55 to +120	$^{\circ}$ C
Short Circuit Output Current	IOS	50	mA

* Maximum Ratings are defined as the limiting conditions that the user can apply to the device under all variations of circuit and environmental conditions. If any rating is exceeded, permanent damage to the device may result. Extended operation at any of these conditions may result in reduced reliability.

** Bonding or soldering of the external pins of these devices can be performed safely at temperatures up to 300 $^{\circ}$ C.

M41256xx-10B, -12B, & -15B Dynamic RAM

Timing Characteristics

(VCC = 5 V \pm 10%, VSS = 0 V, TA = 0 to 70°C) (Notes 1, 2, and 3)

Description	Symbol	JEDEC Symbol	M41256xx-10B		M41256xx-12B		M41256xx-15B		Unit
			Min	Max	Min	Max	Min	Max	
Random Read/Write Cycle Time	tRC	tRELREL	200	—	220	—	260	—	ns
Access Time from \overline{RE} (Notes 4 & 5)	tRAC	tRELQV	—	100	—	120	—	150	ns
Access Time from \overline{CE} (Notes 5 & 6)	tCAC	tCELQV	—	50	—	60	—	75	ns
Output Buffer Turn Off Delay (Note 7)	tOFF	tCEHQZ	0	20	0	30	0	30	ns
Transition Time	tT	tT	2	50	2	50	2	50	ns
\overline{RE} Precharge Time	tRP	tREHREL	90	—	90	—	100	—	ns
\overline{RE} Pulse Width	tRAS	tRELREH	100	10000	120	10000	150	10000	ns
\overline{RE} Hold Time	tRSH	tCELREH	50	—	60	—	75	—	ns
\overline{CE} Pulse Width (Note 8)	tCAS	tCELCEH	50	10000	60	10000	75	10000	ns
\overline{CE} Hold Time	tCSH	tRELCEH	100	—	120	—	150	—	ns
\overline{RE} to \overline{CE} Delay (Note 4)	tRCD	tRELCEL	25	50	25	60	25	75	ns
\overline{CE} to \overline{RE} Precharge Time	tCRP	tCEHREL	0	—	0	—	0	—	ns
Row Address Setup Time	tASR	tRAVREL	0	—	0	—	0	—	ns
Row Address Hold Time	tRAH	tRELRAH	15	—	15	—	15	—	ns
Column Address Setup Time	tASC	tCAVCEL	0	—	0	—	0	—	ns
Column Address Hold Time	tCAH	tCELCAH	15	—	20	—	25	—	ns
Column Address Hold Time Ref. to \overline{RE}	tAR	tRELCAH	75	—	90	—	105	—	ns
Read Command Hold Time Ref. to \overline{RE}	tRRH	tREHWX	10	—	10	—	10	—	ns
Read Command Setup Time	tRCS	tWHCEL	0	—	0	—	0	—	ns
Read Command Hold Time Ref. to \overline{CE}	tRCH	tCEHWX	0	—	0	—	0	—	ns
Write Command Hold Time	tWCH	tCELWX	15	—	20	—	25	—	ns
Write Command Hold Time Ref. to \overline{RE}	tWCR	tRELWX	85	—	100	—	120	—	ns
Write Command Pulse Width	tWP	tWLWH	15	—	20	—	25	—	ns
Write Command to \overline{RE} Lead Time	tRWL	tWLREH	30	—	35	—	45	—	ns
Write Command to \overline{CE} Lead Time	tCWL	tWLCEH	20	—	30	—	40	—	ns
Data In Setup Time	tDS	tDVCEL	0	—	0	—	0	—	ns
Data In Hold Time	tDH	tCELDX	15	—	20	—	25	—	ns
Data In Hold Time Ref. to \overline{RE}	tDHR	tRELDX	85	—	100	—	120	—	ns
Write Command Setup Time (Note 9)	tWCS	tWLCEL	0	—	0	—	0	—	ns
\overline{CE} to \overline{W} Delay (Read-Modify-Write)	tCWD	tCELWL	25	—	30	—	35	—	ns
\overline{RE} to \overline{W} Delay (Read-Modify-Write) (Note 6)	tRWD	tRELWL	75	—	100	—	125	—	ns
Data In Hold Time (Read-Modify-Write) (Note 6)	tDH	tWLDX	20	—	20	—	20	—	ns
Data In Setup Time (Read-Modify-Write)	tDS	tDVWL	0	—	0	—	0	—	ns
Refresh Period	tREF	tR	—	4.0	—	4.0	—	4.0	ms
Cycle Time (Read-Modify-Write)	tRMW	tWRELREL	245	—	260	—	310	—	ns

M41256xx-10B, -12B, & -15B Dynamic RAM

Description	Symbol	JEDEC Symbol	M41256xx-10B		M41256xx-12B		M41256xx-15B		Unit
			Min	Max	Min	Max	Min	Max	
PAGE MODE OPTION									
Page Mode Cycle Time	tPC	tCELCEL	120	—	130	—	145	—	ns
CE Precharge Time	tCP	tCEHCEL	45	—	50	—	60	—	ns
NIBBLE MODE OPTION									
\overline{CE} Cycle Time	tNC	tNCELCEL	50	—	60	—	70	10000	ns
Access Time from \overline{CE} (Notes 5 & 6)	tNCAC	tNCELQV	—	20	—	25	—	30	ns
\overline{RE} Hold Time	tNRRSH	tNCELREH	20	10000	25	10000	30	10000	ns
CE Pulse Width	tCAS	tNCELCEH	20	10000	25	10000	30	10000	ns
Write Command Hold Time	tWCH	tNCELWX	10	—	10	—	10	—	ns
Write Command to \overline{RE} Lead Time	tNRWL	tNWLREH	20	—	25	—	30	—	ns
Write Command to \overline{CE} Lead Time	tNCWL	tNWLCEH	20	—	25	—	30	—	ns
Write Command Pulse Width	tNWP	tNWLWH	10	—	10	—	10	—	ns
Data In Hold Time	tDH	tNCELDX	10	—	10	—	10	—	ns
CE Precharge Time	tNCP	tNCEHCEL	20	—	25	—	30	—	ns
CE to \overline{W} Delay (Read-Modify-Write)	tNCWD	tNCELWL	10	—	15	—	15	—	ns
Data In Hold Time (Read-Modify-Write) (Note 6)	tDH	tNWLDX	10	—	10	—	10	—	ns
\overline{CE} Before \overline{RE} Refresh	tFCS	tCELREL	10	—	10	—	10	—	ns
CE to \overline{RE} Delay	tFCH	tRELCEX	20	—	25	—	30	—	ns
CE Hold Time	tRPC	tREHCEL	0	—	0	—	0	—	ns
\overline{RE} Precharge to \overline{CE} Active									

Notes:

- Timing specifications given assume $t_T = 5$ ns.
- V_{IH} (min.), V_{IL} (max.) are reference levels for timing specifications or input signals. Transition times are to be measured between these reference levels.
- An initial pause of 100 μ s followed by a minimum of 8 refresh cycles is necessary after VCC is applied, to achieve proper device operation. Addresses A0–A7 are used for refresh. A8 must be a valid one or zero.
- For $t_{RELCEL} > t_{RELCEL}(\text{max.})$, t_{RELQV} will increase by the amount that $t_{RELCEL}(\text{max.})$ is exceeded.
- Q load assumed to be equivalent to 2 TTL loads and 100 pF.
- Assumes $t_{RELCEL} \geq t_{RELCEL}(\text{max.})$.
- $t_{CEHQZ}(\text{max.})$ defines the time at which Q achieves the open circuit condition.
- \overline{CE} can be held at Logic 0 for an indefinite time for latched output during refresh. However, t_{RELRAx} must be increased to 100 ns.
- Non-restrictive operating parameter. If $t_{WLCEL} \geq t_{WLCEL}(\text{min.})$, the cycle is an early write cycle and the data out (Q) will remain an open circuit (high impedance) for the entire cycle. If $t_{CELWL} \geq t_{CELWL}(\text{min.})$ and $t_{RELWL} \geq t_{RELWL}(\text{min.})$, the cycle is a read-write cycle and the data out (Q) will validly reproduce the data contained in the selected cell. If neither of the above sets or conditions is satisfied, data out will be indeterminate.

M41256xx-10B, -12B, & -15B Dynamic RAM

Timing Diagrams

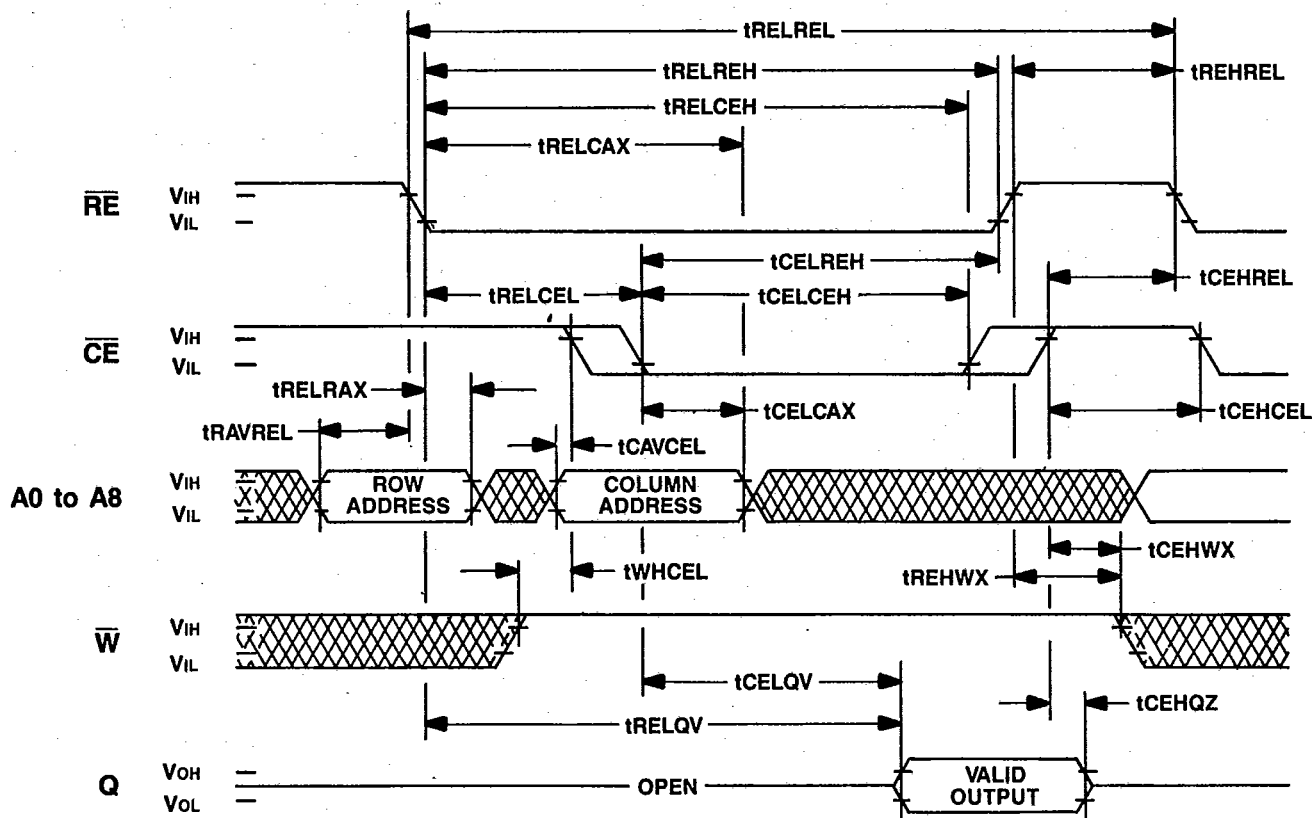


Figure 4. Read Cycle

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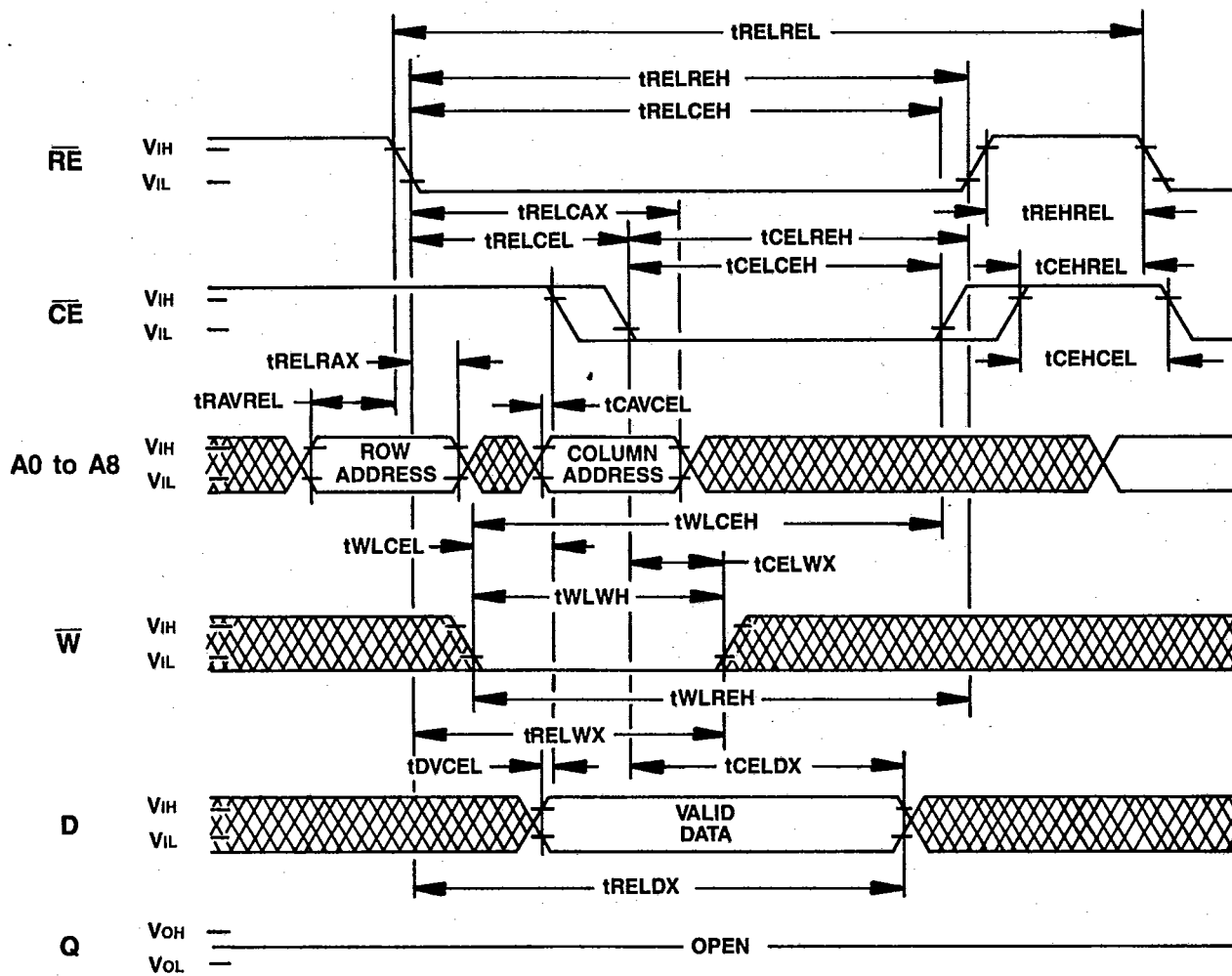


Figure 5. Write Cycle (Early Write)

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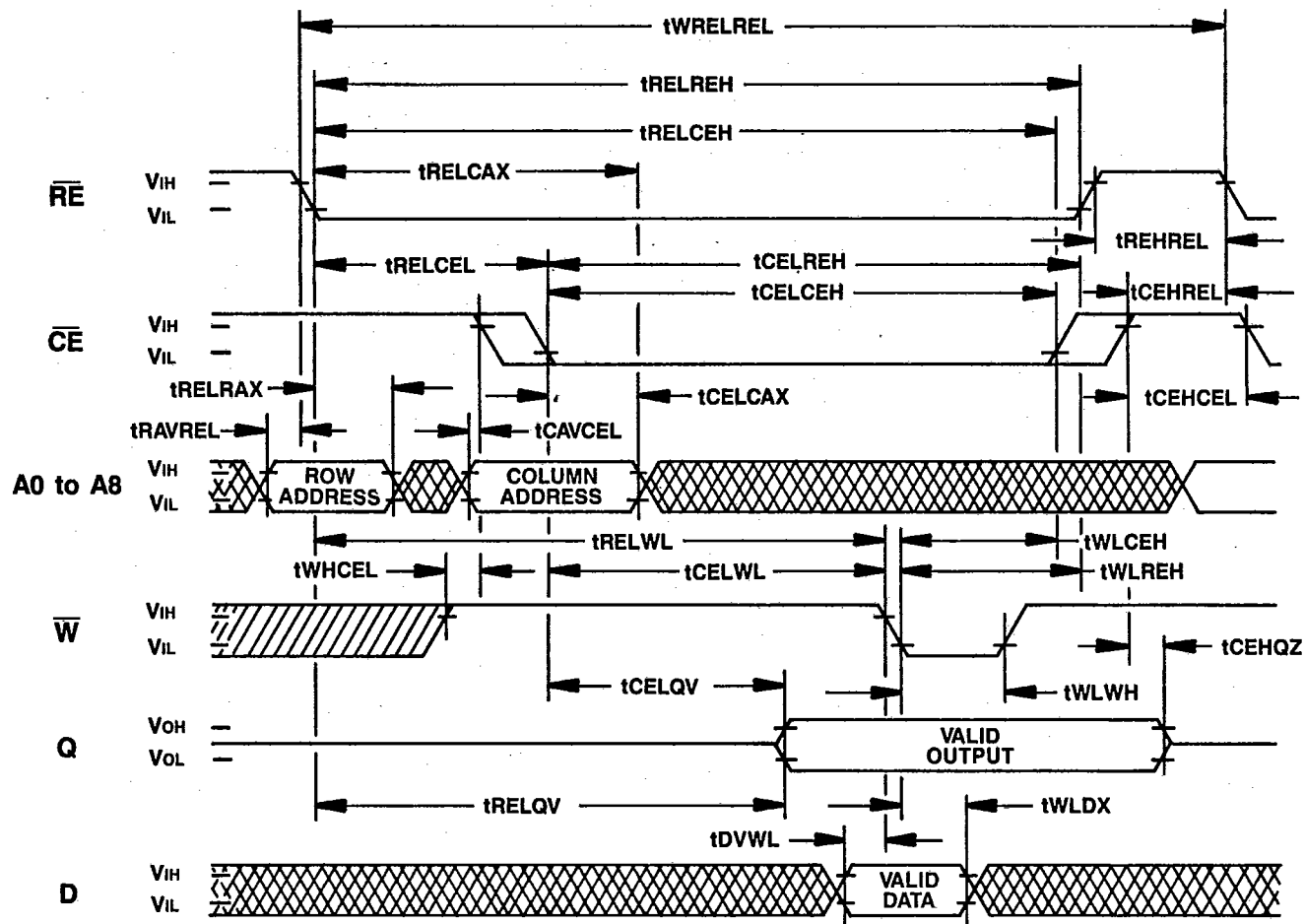
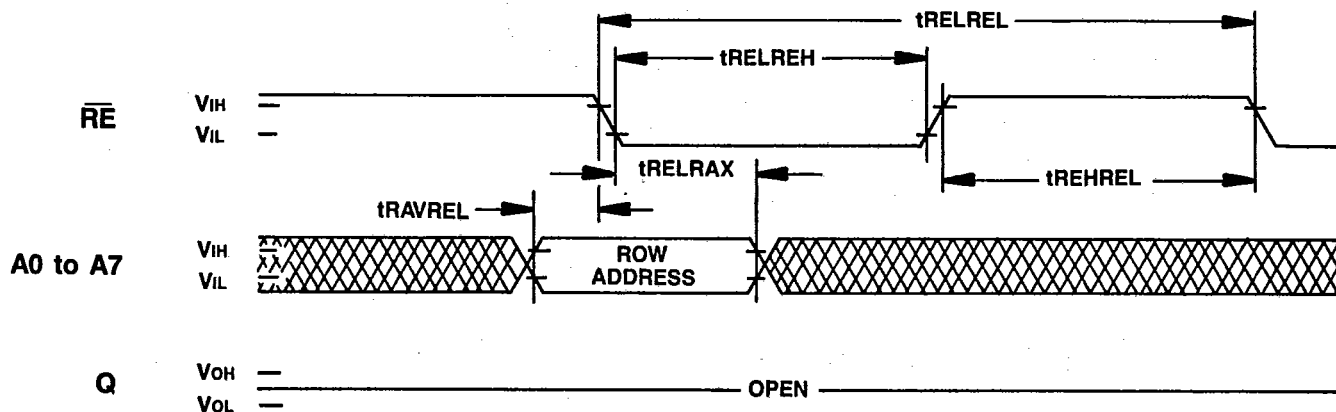


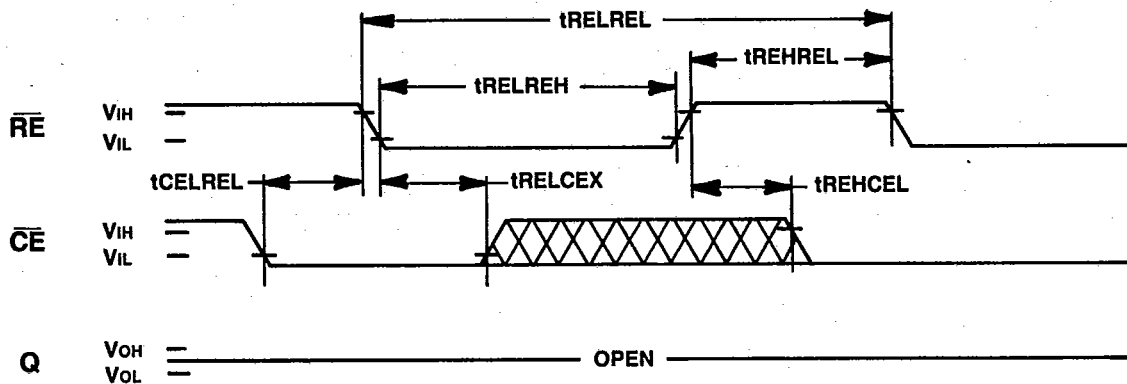
Figure 6. Read-Modify-Write Cycle



NOTE: Input $\overline{CE} \geq V_{IH}$, Input $\overline{W} = \text{Don't Care}$

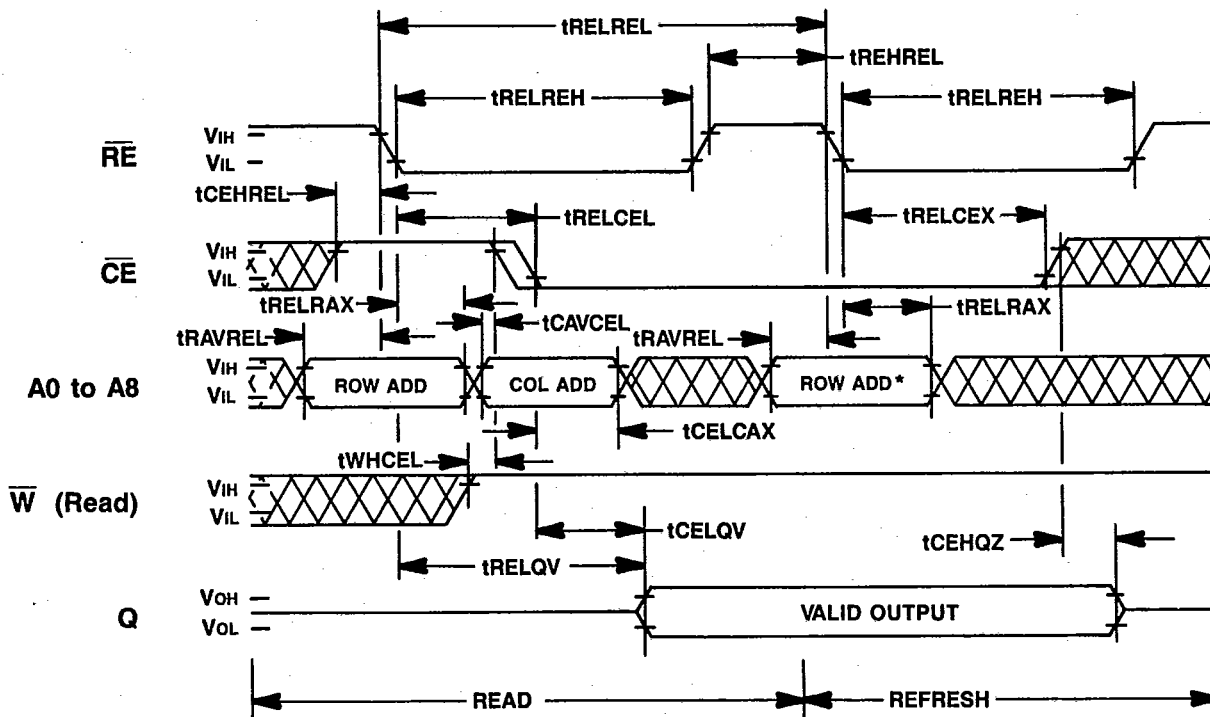
Figure 7. \overline{RE} Only Refresh Cycle (Note 3)

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NOTE: Inputs A0–A8, \overline{W} , D = Don't Care

Figure 8. \overline{CE} Before \overline{RE} Refresh Cycle (Available with Nibble Mode Option Only)



* This row address not necessary when using a device with \overline{CE} before \overline{RE} refresh (as available with the nibble mode part).

Figure 9. Hidden Refresh Cycle (Notes 3 & 8)

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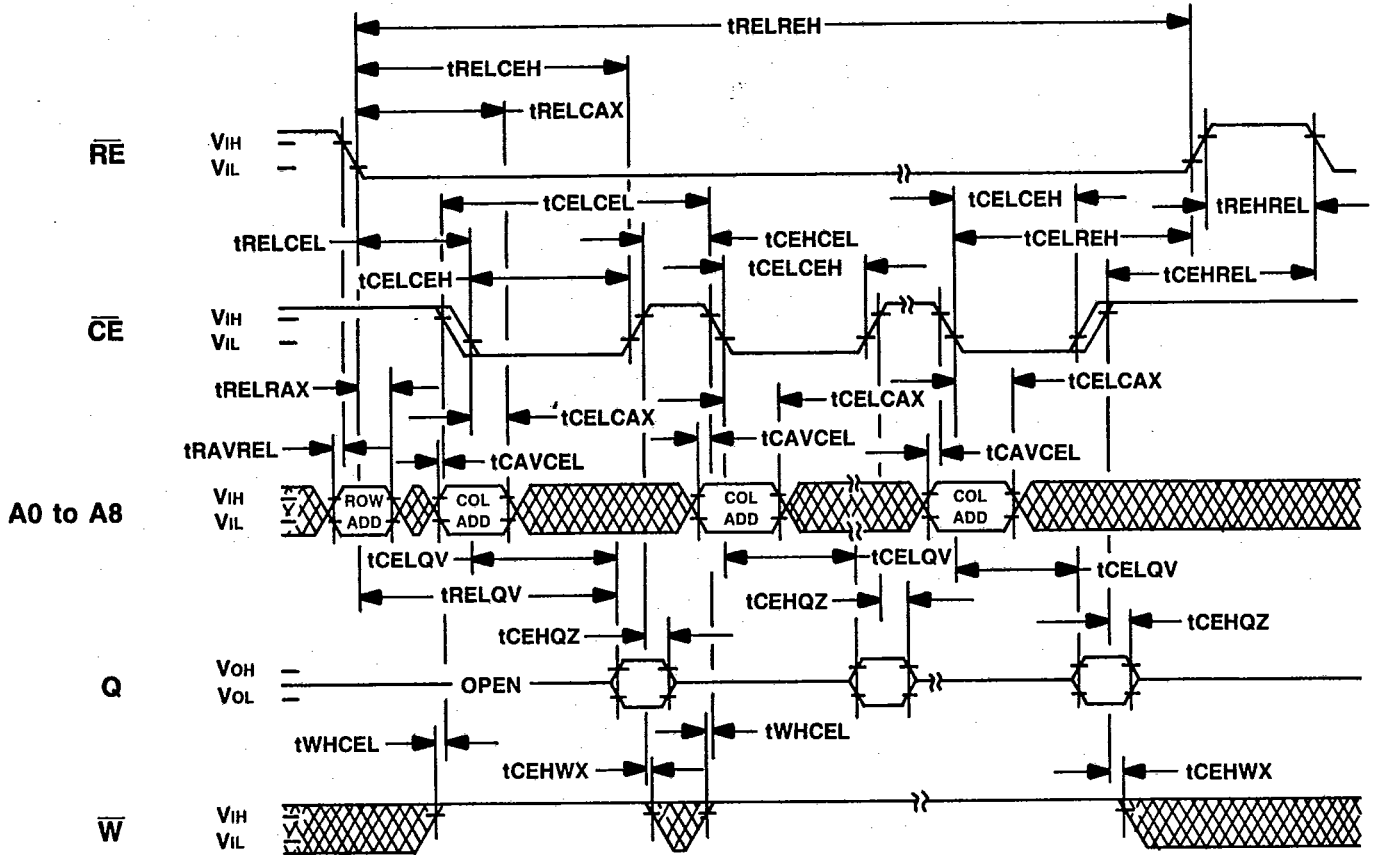


Figure 10. Page Mode Read Cycle

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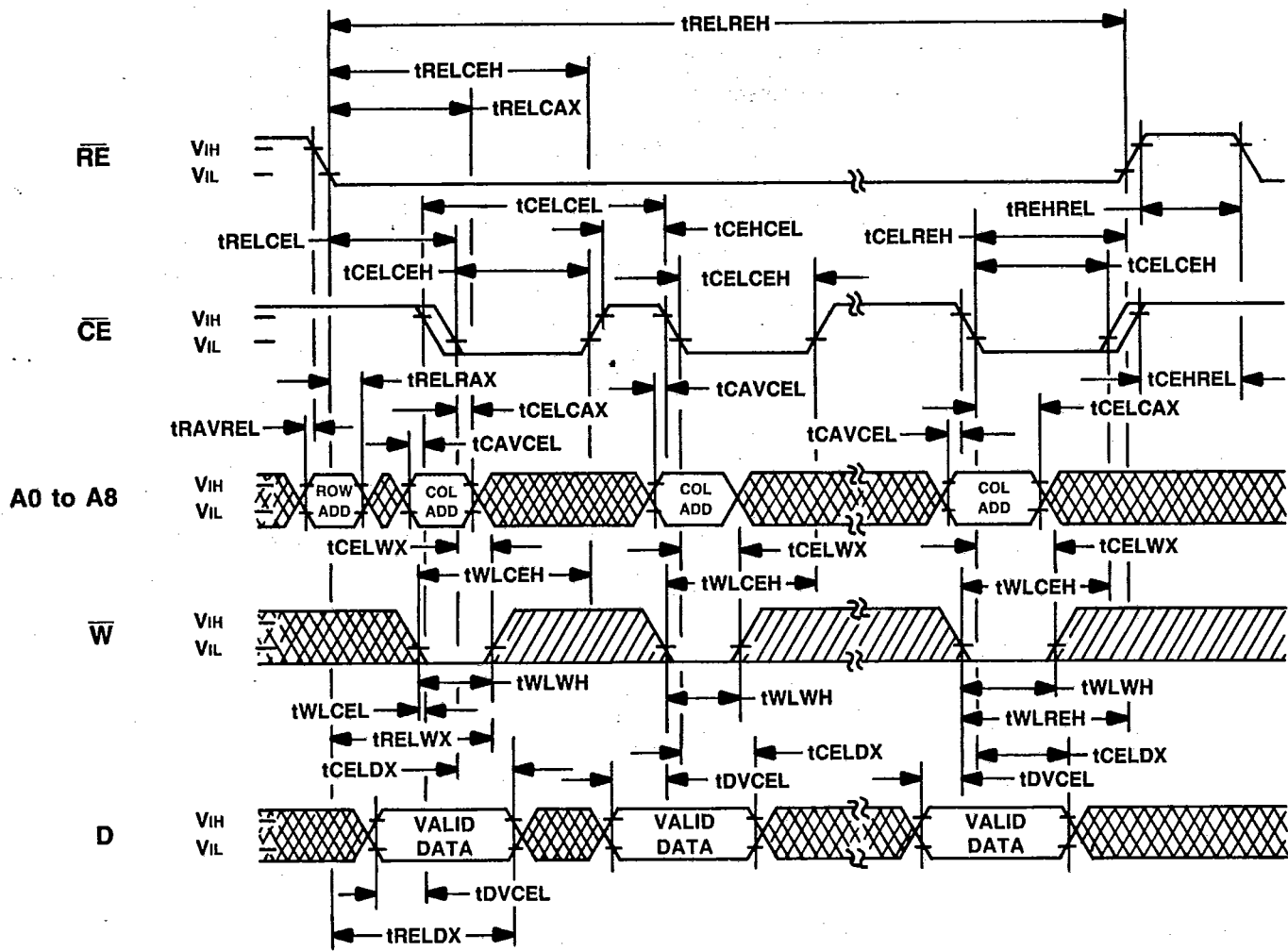


Figure 11. Page Mode Write Cycle

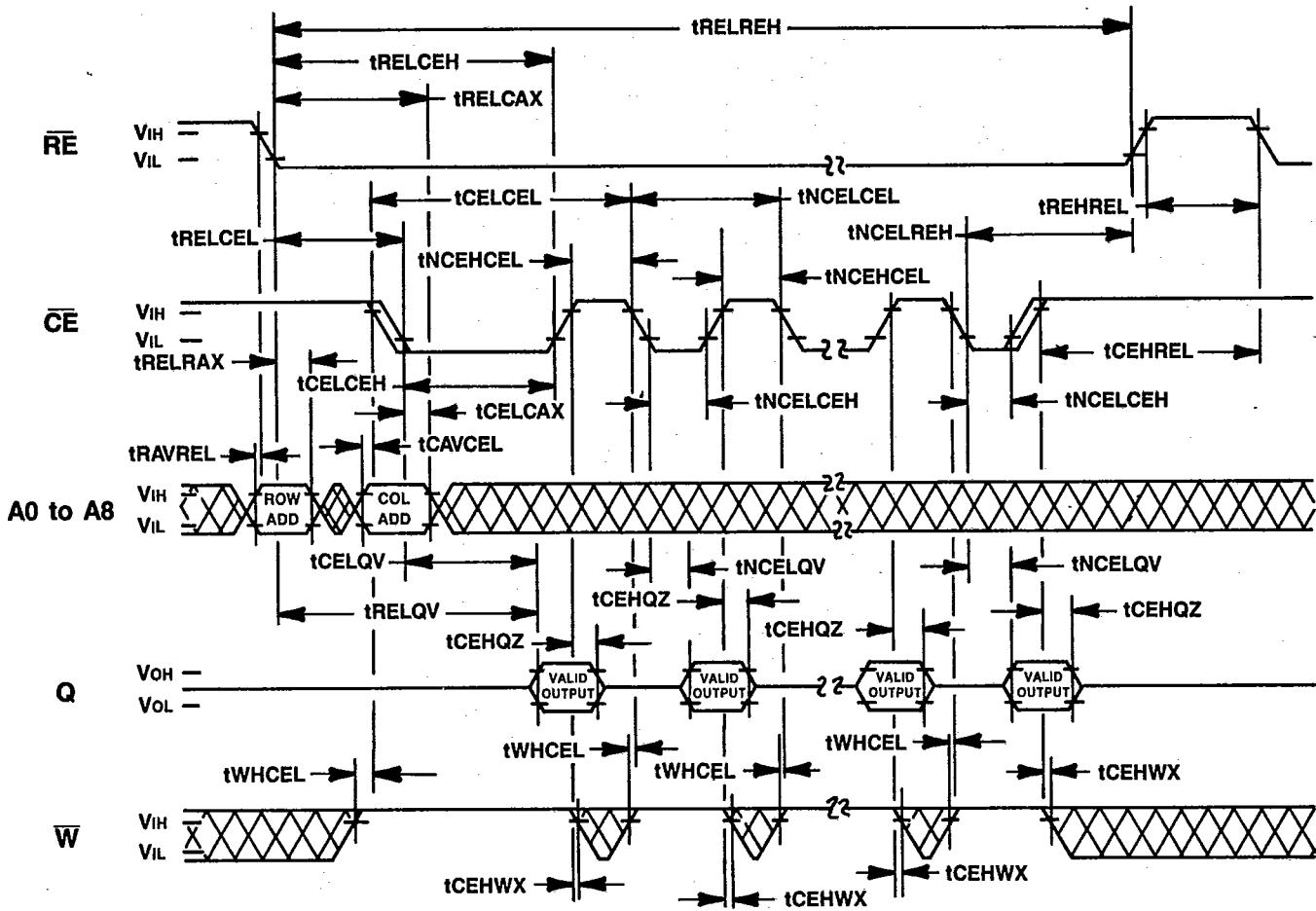


Figure 13. Nibble Mode Read Cycle

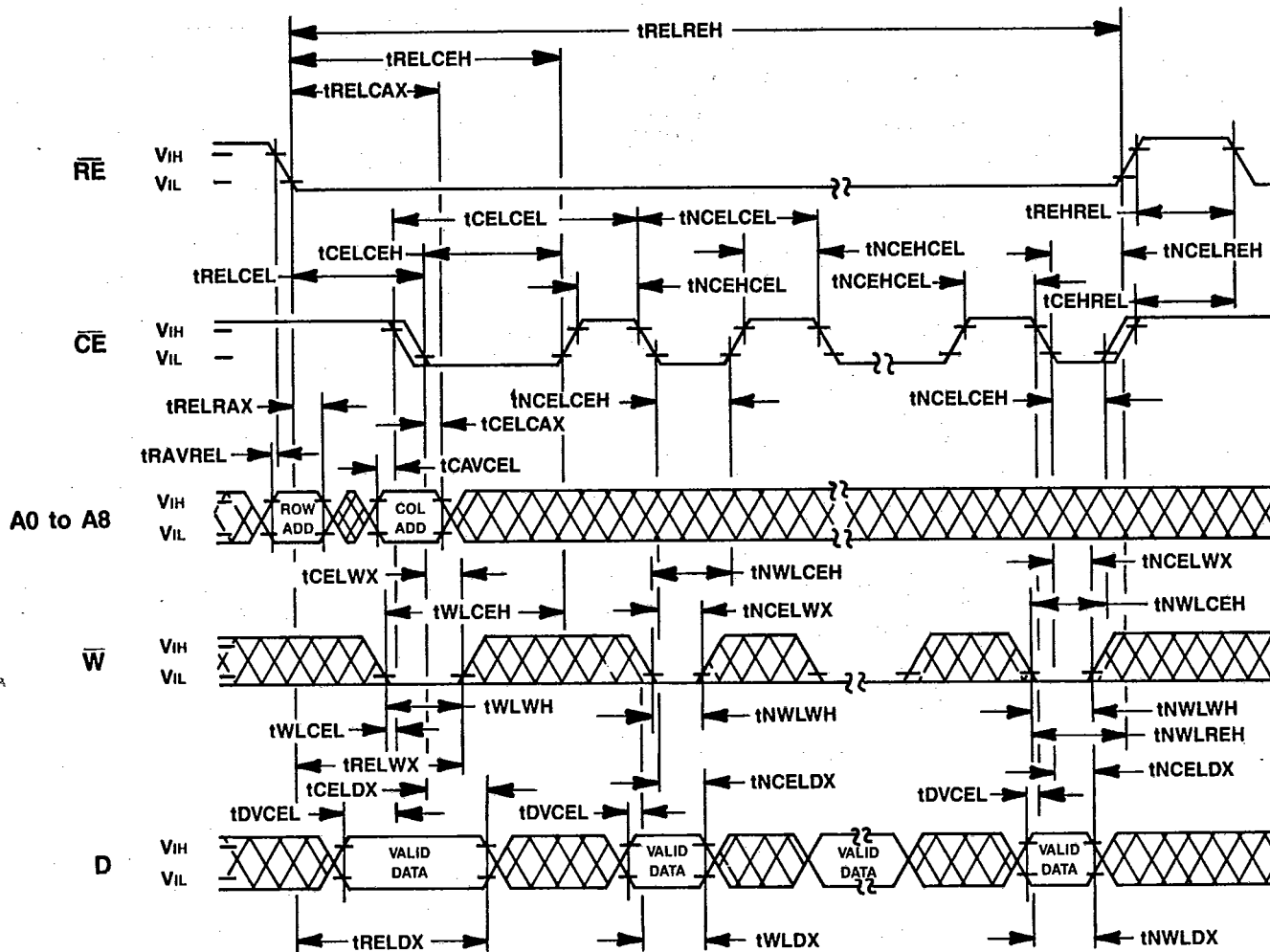


Figure 14. Nibble Mode Write Cycle

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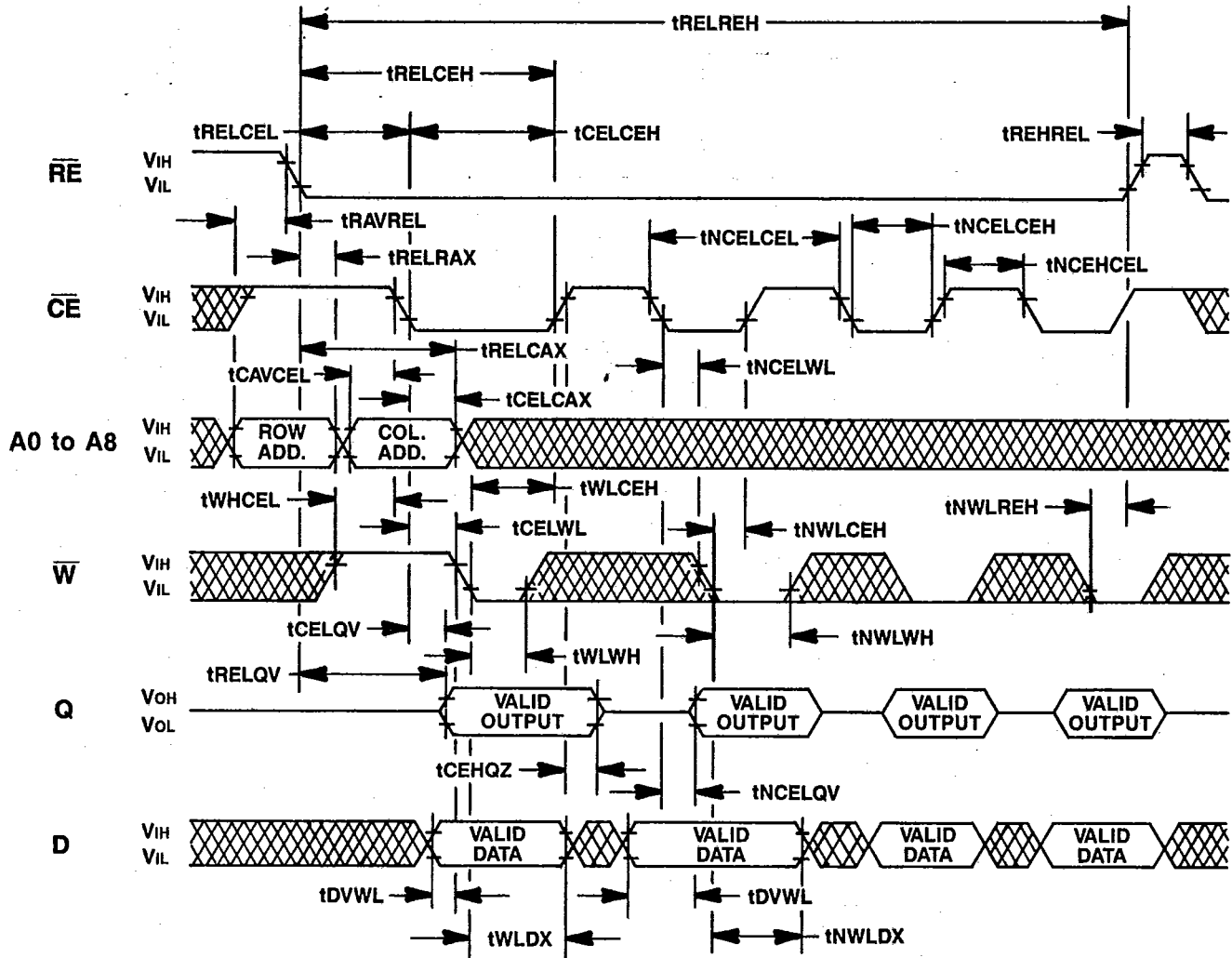
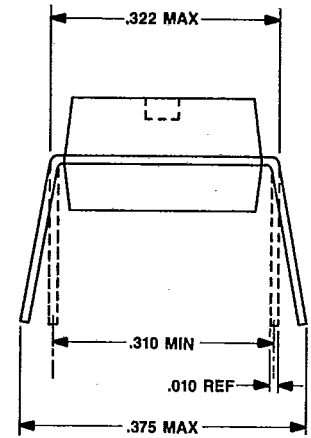
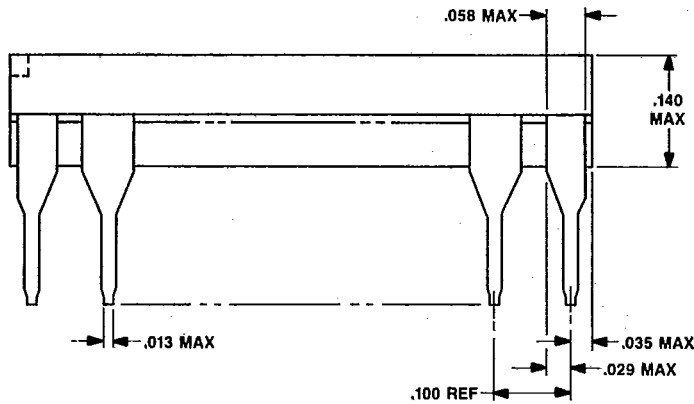
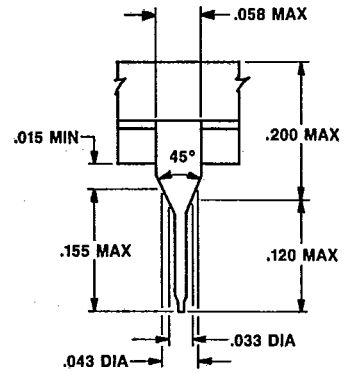
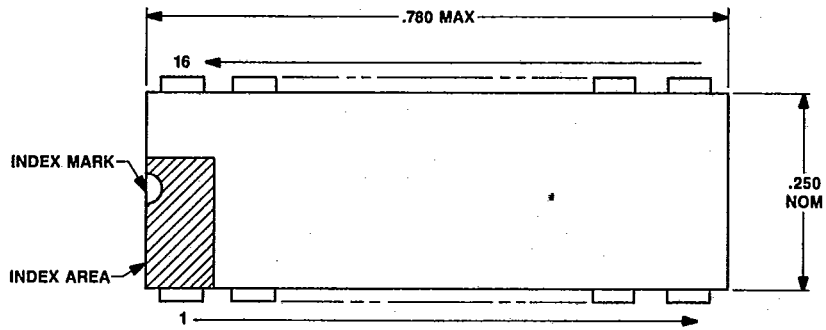


Figure 15. Nibble Mode Read-Modify-Write Cycle

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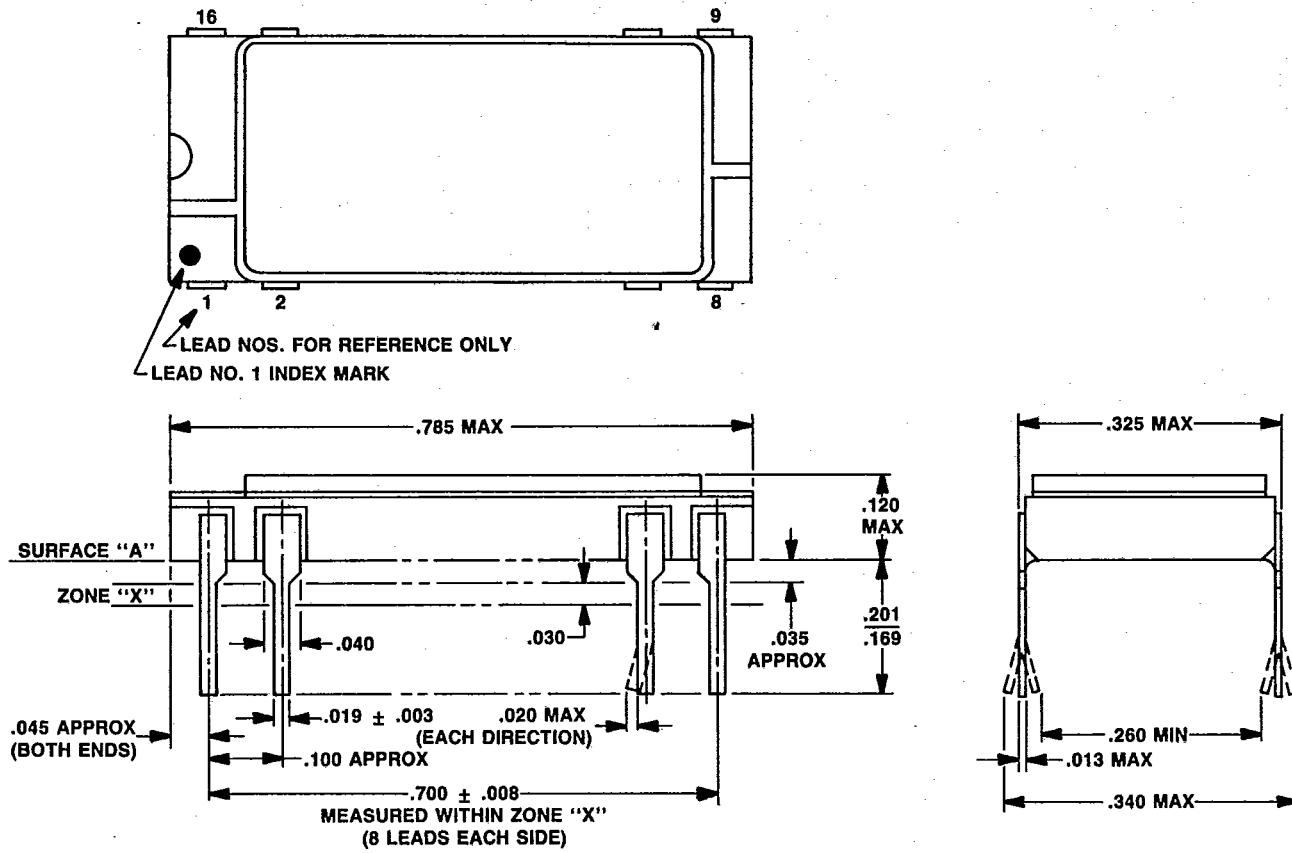
OUTLINE DRAWINGS (Dimensions in Inches)

16-Pin Plastic DIP



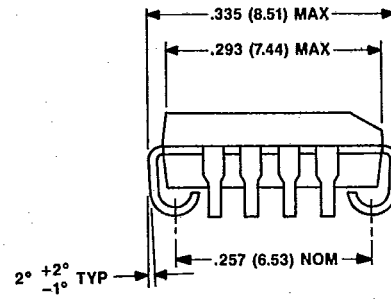
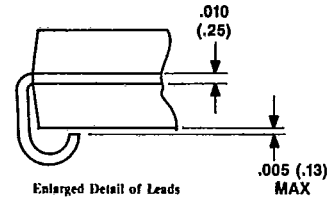
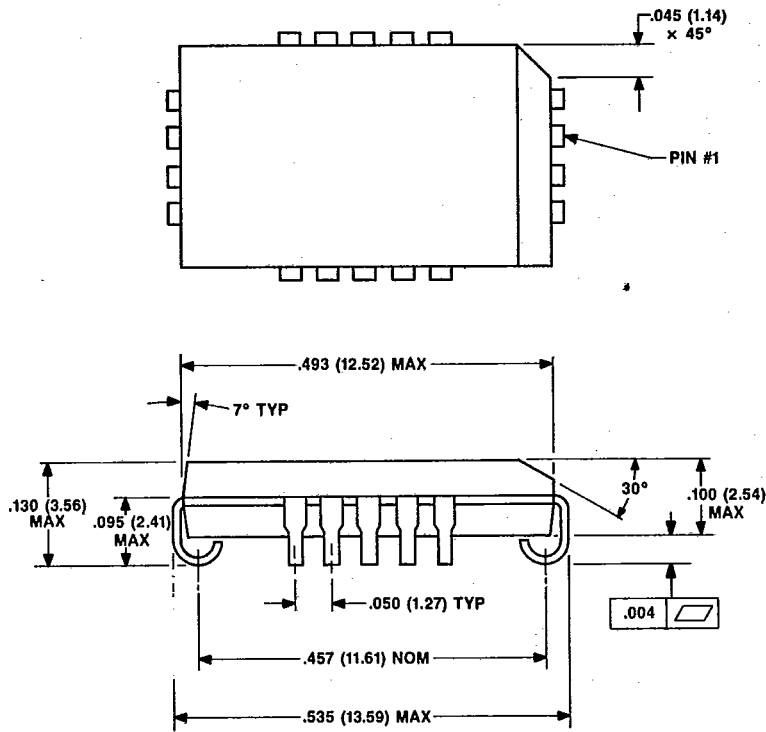
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16-Pin Hermetic Ceramic DIP



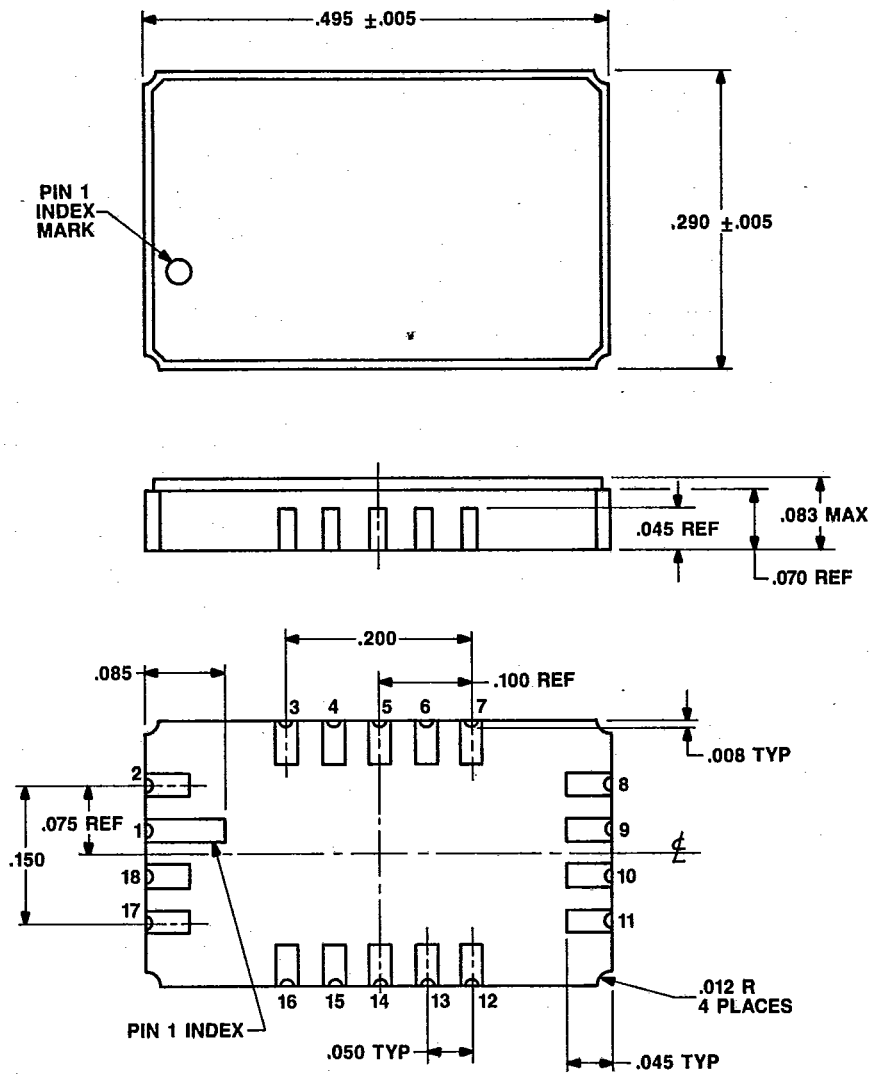
M41256xx-10B, -12B, & -15B Dynamic RAM

18 I/O Plastic Leaded Chip Carrier



M41256xx-10B, -12B, & -15B Dynamic RAM

18 I/O Ceramic Leadless Chip Carrier (Hermetic)



M41256xx-10B, -12B, & -15B Dynamic RAM**ORDERING INFORMATION**

Package	Mode	Part Number	COMCODE
PLCC	Page	M41256DP-10B*	104382395
		M41256DP-12B	104370358
		M41256DP-15B	104370366
Plastic DIP	Page	M41256PP-10B*	104375159
		M41256PP-12B	104375167
		M41256PP-15B	104375175
Ceramic LCC	Page	M41256CP-10B*	104382239
		M41256CP-12B	104382247
		M41256CP-15B	104382254
Ceramic DIP	Page	M41256HP-10B*	104382320
		M41256HP-12B	104375092
		M41256HP-15B	104375100
Ceramic LCC	Nibble	M41256CN-10B*	104382213
		M41256CN-12B	104387618
		M41256CN-15B	104382221
Ceramic DIP	Nibble	M41256HN-10B*	104382312
		M41256HN-12B	104375076
		M41256HN-15B	104375084

* Limited Quantities

T-46-23-15

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 AT&T Technologies, 555 Union Boulevard, Dept. 50AL203140, Allentown, PA 18103
1-800-372-2447

In Europe, contact:
 AT&T Microelectronics, Freischützstrasse 92, 8000 München 81, West Germany
Tel. 0 89/95 97 0 Telex 5 216 884

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